

L Number	Hits	Search Text	DB	Time stamp
1	1	5854708.pn.	USPAT	2003/04/25 08:05
2	0	5854708.pn. and dop\$3	USPAT	2003/04/25 08:05
3	7	photocatalytic same semiconductor same dop\$3	USPAT	2003/04/25 08:13
4	26	photocatalytic same oxide same dop\$3	USPAT	2003/04/25 08:41
5	10	(photocatalytic or photocatylst) same oxide same dop\$3 same fluorine	USPAT	2003/04/25 08:42
-	1	5698262.pn.	USPAT	2003/04/24 13:20
-	1	4377613.pn.	USPAT	2002/10/28 09:07
-	2	5698262.pn. or 4377613.pn.	USPAT	2002/10/28 09:07
-	2	01014129.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/10/28 10:48
-	16	(((((indium near3 tin near3 oxide) or ITO) with ((silicon adj (oxide or dioxide)) or ("SiO.sub.2")))) and (glass with substrate)) and (emissivity and transmittance)	USPAT	2002/10/28 11:20
-	14	(((((indium near3 tin near3 oxide) or ITO) with ((silicon adj (oxide or dioxide)) or ("SiO.sub.2")))) and (glass with substrate)) and ((silicon adj (oxide or dioxide)) or ("SiO.sub.2")) with outer	USPAT	2002/10/28 11:26
-	1408	((indium near3 tin near3 oxide) or ITO) with ((silicon adj (oxide or dioxide)) or ("SiO.sub.2"))	USPAT	2002/10/28 11:31
-	849	((indium near3 tin near3 oxide) or ITO) with ((silicon adj (oxide or dioxide)) or ("SiO.sub.2")) and (glass with substrate)	USPAT	2002/10/28 11:43
-	8	((indium with tin with oxide with fluorine) or (ITO with fluorine)) with ((silicon adj (oxide or dioxide)) or ("SiO.sub.2"))	USPAT	2002/10/28 11:41
-	1592	(tin adj oxide) with ((silicon adj (oxide or dioxide)) or ("SiO.sub.2"))	USPAT	2002/10/28 11:42
-	686	(tin adj oxide) with ((silicon adj (oxide or dioxide)) or ("SiO.sub.2")) with (layer or film)	USPAT	2002/10/28 11:43
-	1106	((tin adj oxide) or ("SnO.sub.2")) with ((silicon adj (oxide or dioxide)) or ("SiO.sub.2")) with (layer or film)	USPAT	2002/10/28 11:44
-	617	((tin adj oxide) or ("SnO.sub.2")) with ((silicon adj (oxide or dioxide)) or ("SiO.sub.2")) with (layer or film) and (glass with substrate)	USPAT	2002/10/28 11:43
-	43	((tin adj oxide) or ("SnO.sub.2")) with ((silicon adj (oxide or dioxide)) or ("SiO.sub.2")) with (layer or film) and (glass with substrate) and ((silicon adj (oxide or dioxide)) or ("SiO.sub.2")) with outer	USPAT	2002/10/28 11:44
-	12	(annette same krisko).in.	USPAT	2002/10/28 13:23
-	0	(bob same bond).in.	USPAT	2002/10/28 13:23
-	1	(roger same stanek).in.	USPAT	2002/10/28 13:24
-	2	(gary same pfaff).in.	USPAT	2002/10/28 13:24
-	41	(klaus same hartig).in.	USPAT	2002/10/28 13:24

-	1	6156598.pn.	USPAT	2003/04/24 08:09
-	0	6156598.pn. and sputter\$3	USPAT	2003/04/24 08:09
-	1	6165598.pn.	USPAT	2003/04/24 08:09
-	0	6165598.pn. and sputter\$3	USPAT	2003/04/24 08:09
-	0	outer with sputter\$3 with ((silicon adj (oxide or dioxide)) or silica) with (layer or film) with (contact adj angle)	USPAT	2003/04/24 08:35
-	1	outer with ((silicon adj (oxide or dioxide)) or silica) with (layer or film) with (contact adj angle)	USPAT	2003/04/24 08:33
-	12	outer with sputter\$3 with ((silicon adj (oxide or dioxide)) or silica) with (layer or film)	USPAT	2003/04/24 08:35
-	3	sputter\$3 with ((silicon adj (oxide or dioxide)) or silica) with (layer or film) with (contact adj angle)	USPAT	2003/04/24 08:41
-	0	(CVD or (chemical adj vapor)) with ((silicon adj (oxide or dioxide)) or silica) with (layer or film) with (contact adj angle)	USPAT	2003/04/24 08:40
-	0	sputter\$3 same ((silicon adj (oxide or dioxide)) or silica) same (layer or film) same (contact adj angle) same ((CVD) or (chemical adj vapor adj deposition))	USPAT	2003/04/24 08:43
-	2	sputter\$3 same ((silicon adj (oxide or dioxide)) or silica) same (layer or film) same (contact adj angle) same ((CVD) or (chemical adj vacuum adj deposition))	USPAT	2003/04/24 08:43
-	1	6261700.pn.	USPAT	2003/04/24 11:22
-	2	9631343.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/24 11:23
-	510	outer near2 (silica or (silcon adj (oxide or dioxide)))	USPAT	2003/04/24 11:36
-	192	outer near2 (silica or (silcon adj (oxide or dioxide))) with (layer or film)	USPAT	2003/04/24 11:36
-	128	(outer near2 (silica or (silcon adj (oxide or dioxide))) with (layer or film)) and glass	USPAT	2003/04/24 11:44
-	18	((outer near2 (silica or (silcon adj (oxide or dioxide))) with (layer or film)) and glass) and dielectric	USPAT	2003/04/24 11:36
-	21	(outer near2 (silica or (silcon adj (oxide or dioxide))) with (layer or film)) and (glass with substrate)	USPAT	2003/04/24 11:46
-	1	4966437.pn.	USPAT	2003/04/24 11:46
-	0	4966437.pn. and sputter\$4	USPAT	2003/04/24 11:47
-	1	4966437.pn. and (chemical or vapor)	USPAT	2003/04/24 11:47
-	1	4966437.pn. and deposit\$3	USPAT	2003/04/24 11:47
-	1	4966437.pn. and deposit\$4	USPAT	2003/04/24 11:50
-	103	(silica or silicon adj (oxide or dioxide)) with (contact adj angle)	USPAT	2003/04/24 11:50
-	43	(silica or silicon adj (oxide or dioxide)) with (contact adj angle) with (layer or film)	USPAT	2003/04/24 11:50
-	7	(silica or silicon adj (oxide or dioxide)) with (contact adj angle) with (layer or film) same (thick or thickness or angstroms)	USPAT	2003/04/24 11:50

-	4	820967.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT	2003/04/24 11:59
-	1	5854708.pn.	USPAT	2003/04/24 12:17
-	0	5854708.pn. and angle	USPAT	2003/04/24 12:17
-	1	5854708.pn. and contact	USPAT	2003/04/24 12:17
-	1	5633208.pn.	USPAT	2003/04/24 13:20